

Title (en)
RESIST SYSTEM, USE OF A RESIST SYSTEM AND LITHOGRAPHY METHOD FOR THE PRODUCTION OF SEMICONDUCTOR ELEMENTS

Title (de)
RESISTSYSTEM, VERWENDUNG EINES RESISTSYSTEMS UND LITHOGRAPHIEVERFAHREN ZUR HERSTELLUNG VON HALBLEITERBAUELEMENTEN

Title (fr)
SYSTEME DE RESERVE, UTILISATION D'UN SYSTEME DE RESERVE ET PROCEDE DE LITHOGRAPHIE DESTINE A LA FABRICATION DE COMPOSANTS A SEMICONDUCTEURS

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Abstract (en)
[origin: WO2004031858A2] The invention relates to a resist system for lithography methods for the production of semiconductor components at wavelengths of 0.1 -150 nm, characterised by at least one polymer or copolymer comprising at least one acid-labile group. The invention also relates to the use of a resist system and a lithography method, whereby it is possible to obtain high sensitivity, especially in the EUV range, and no limitation of the process window occurs by undesirable cross-linking in the resist system, even at high doses of exposure. .

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